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The invention relates to photodetectors on base of semiconductors, in particular to photodetectors of ultra-violet radiation and may be used in optoelectronic systems for determining the intensity and dose of ultra-violet radiation emitted by the Sun or other sources.

Summary of the invention consists in the fact that in the photodetector of ultra-violet radiation the superficial potential barrier is divided into two identical elements, electrically isolated each of the other, one of them being covered with a layer of transparent material for visible and infra-red radiation and absorbing the ultra-violet radiation.

The technical result consists in mutual compensation of visible and infra-red components of the radiation spectrum.